NLSX3378

4-Bit 20 Mb/s Dual-Supply Level Translator

The NLSX3378 is a 4−bit configurable dual−supply bidirectional auto sensing translator that does not require a directional control pin. The V_{CC} I/O and V_L I/O ports are designed to track two different power supply rails, V_{CC} and V_L respectively. The V_{CC} supply rail is configurable from 1.65 V to 4.5 V while V_L supply rail is configurable to 1.2 V to 4.1 V. This allows lower voltage logic signals on the V_L side to be translated into higher voltage logic signals on the V_{CC} side, and vice−versa.

The NLSX3378 translator has open−drain outputs with integrated 10 kΩ pullup resistors on the I/O lines. The integrated pullup resistors are used to pullup the I/O lines to either V_L or V_{CC}. The NLSX3378 is an excellent match for open−drain applications such as the I^2C communication bus.

Features

- Wide High−Side V_{CC} Operating Range: 1.65 V to 4.5 V
  Wide Low−Side V_L Operating Range: 1.2 V to 4.1 V
- High−Speed with 20 Mb/s Guaranteed Date Rate for V_L > 2.5 V
- Low Bit−to−Bit Skew
- Enable Input and I/O Lines have Overvoltage Tolerant (OVT) to 4.5 V
- Nonpreferential Powerup Sequencing
- Integrated 10 kΩ Pullup Resistors
- Small Space Saving Package − 2.02 x 1.54 mm μBump12
- This is a Pb−Free Device

Typical Applications

- I^2C, SMBus, PMBus
- Low Voltage ASIC Level Translation
- Mobile Phones, PDAs, Cameras

Important Information

- ESD Protection for Power, Enable and I/O Pins:
  Human Body Model (HBM): ±2 kV

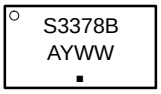
ON Semiconductor®

www.onsemi.com

μBump12
FC SUFFIX
CASE 499AU

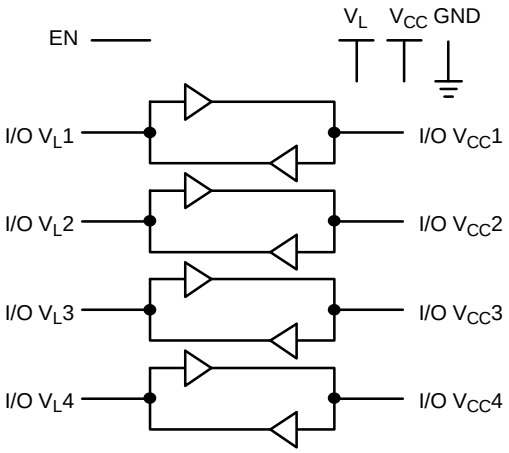
MARKING DIAGRAM
for NLSX3378FCT1G

for NLSX3378BFCT1G



A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

LOGIC DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

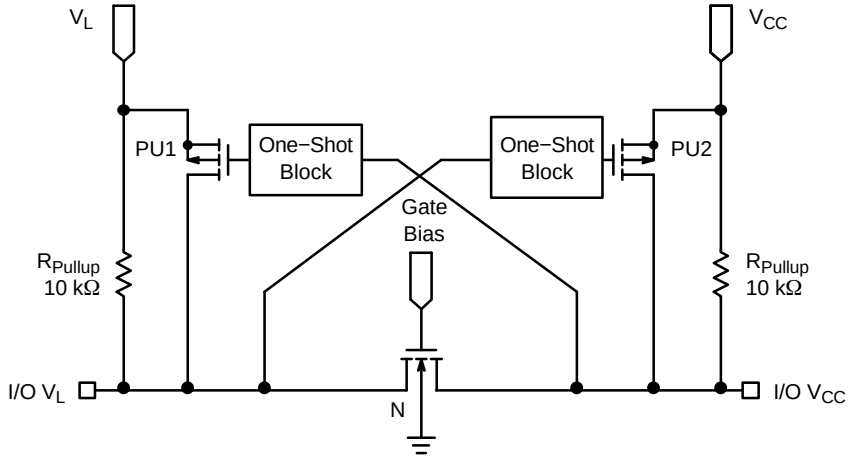


Figure 1. Block Diagram (1 I/O Line)

PIN ASSIGNMENT

Pins	Description
V_{CC}	V_{CC} Input Voltage
V_L	V_L Input Voltage
GND	Ground
EN	Output Enable
I/O V_{CC}n	V_{CC} I/O Port, Referenced to V_{CC}
I/O V_Ln	V_L I/O Port, Referenced to V_L

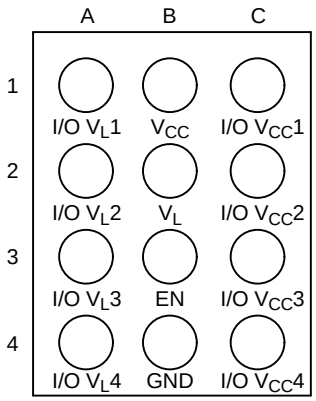
FUNCTION TABLE

EN	Operating Mode
L	Hi−Z
H	I/O Buses Connected

PIN LOCATION

Pin	Pin Name
A1	I/O V_L1
A2	I/O V_L2
A3	I/O V_L3
A4	I/O VL4
B1	V_{CC}
B2	V_L
B3	EN
B4	GND
C1	I/O V_{CC}1
C2	I/O V_{CC}2
C3	I/O V_{CC}3
C4	I/O V_{CC}4

μBump12
(2.02 x 1.54 mm)



(Bottom View)

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V_{CC}	High−side DC Supply Voltage	−0.3 to +7.0		V
V_L	High−side DC Supply Voltage	−0.3 to +7.0		V
I/O V_{CC}	V_{CC}−Referenced DC Input/Output Voltage	−0.3 to (V_{CC} + 0.3)		V
I/O V_L	V_L−Referenced DC Input/Output Voltage	−0.3 to (V_L + 0.3)		V
V_{EN}	Enable Control Pin DC Input Voltage	−0.3 to +7.0		V
I_{I/O_SC}	Short−Circuit Duration (I/O V_L and I/O V_{CC} to GND)	40	Continuous	mA
T_{STG}	Storage Temperature	−65 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	High−side Positive DC Supply Voltage	1.65	4.5	V
V_L	High−side Positive DC Supply Voltage	1.2	4.1	V
V_{EN}	Enable Control Pin Voltage	GND	4.5	V
V_{IO}	Enable Control Pin Voltage	GND	4.5	V
T_A	Operating Temperature Range	−40	+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 1.65 V to 4.5 V and V_L = 1.2 V to 4.1 V, unless otherwise specified)

Symbol	Parameter	Test Conditions	−40°C to +85°C			Unit
			Min	Typ (Notes 1, 2)	Max	
V_{IHC}	I/O V_{CC} Input HIGH Voltage		V_{CC} − 0.4	−	−	V
V_{ILC}	I/O V_{CC} Input LOW Voltage		−	−	0.15	V
V_{IHL}	I/O V_L Input HIGH Voltage		V_L − 0.2	−	−	V
V_{ILL}	I/O V_L Input LOW Voltage		−	−	0.15	V
V_{IH}	Control Pin Input HIGH Voltage		V_L − 0.2	−	−	V
V_{IL}	Control Pin Input LOW Voltage		−	−	0.15	V
V_{OHC}	I/O V_{CC} Output HIGH Voltage	I/O V_{CC} Source Current = 20 μA	2/3 * V_{CC}	−	−	V
V_{OLC}	I/O V_{CC} Output LOW Voltage	I/O V_{CC} Sink Current = 20 μA	−	−	1/3 * V_{CC}	V
V_{OHL}	I/O V_L Output HIGH Voltage	I/O V_L Source Current = 20 μA	2/3 * V_L	−	−	V
V_{OLL}	I/O V_L Output LOW Voltage	I/O V_L Sink Current = 20 μA	−	−	1/3 * V_L	V
I_{QVCC}	V_{CC} Supply Current	I/O V_{CC} and I/O V_L Unconnected, V_{EN} = V_L	−	50	105	μA
I_{QVL}	V_L Supply Current	I/O V_{CC} and I/O V_L Unconnected, V_{EN} = V_L	−	0.1	1.0	μA
I_{TS-VCC}	V_{CC} Tristate Output Mode Supply Current	I/O V_{CC} and I/O V_L Unconnected, V_{EN} = GND	−	0.1	2.5	μA
I_{TS-VL}	V_L Tristate Output Mode Supply Current	I/O V_{CC} and I/O V_L Unconnected, V_{EN} = GND	−	0.1	2.5	μA
I_{OZ}	I/O Tristate Output Mode Leakage Current	T_A = +25°C	−	−	1.0	μA
R_{PU}	Pullup Resistor I/O V_L and V_{CC}	T_A = +25°C	−	10	−	kΩ

1. Typical values are for V_{CC} = +2.8 V, V_L = +1.8 V and T_A = +25°C.
2. All units are production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TIMING CHARACTERISTICS − RAIL−TO−RAIL DRIVING CONFIGURATIONS

(I/O test circuit of Figures 2 and 3, C_{LOAD} = 15 pF, driver output impedance ≤ 50 Ω, R_{LOAD} = 1 MΩ)

Symbol	Parameter	Test Conditions	−40°C to +85°C (Note 3)			Unit
			Min	Typ	Max	
+1.2 ≤ V_L ≤ V_{CC} ≤ +4.5 V						
t_{RVCC}	I/O V_{CC} Risetime				25	ns
t_{FVCC}	I/O V_{CC} Falltime				37	ns
t_{RVL}	I/O V_L Risetime				30	ns
t_{FVL}	I/O V_L Falltime				30	ns
$t_{PDVL−VCC}$	Propagation Delay (Driving I/O V_L)				30	ns
$t_{PDVCC−VL}$	Propagation Delay (Driving I/O V_{CC})				30	ns
t_{PPSKEW}	Part−to−Part Skew				20	nS
MDR	Maximum Data Rate		8			Mb/s
+1.2 ≤ V_L ≤ V_{CC} ≤ +3.3 V						
t_{RVCC}	I/O V_{CC} Risetime				25	ns
t_{FVCC}	I/O V_{CC} Falltime				30	ns
t_{RVL}	I/O V_L Risetime				30	ns
t_{FVL}	I/O V_L Falltime				30	ns
$t_{PDVL−VCC}$	Propagation Delay (Driving I/O V_L)				20	ns
$t_{PDVCC−VL}$	Propagation Delay (Driving I/O V_{CC})				20	ns
t_{PPSKEW}	Part−to−Part Skew				10	nS
MDR	Maximum Data Rate		10			Mb/s
+1.8 ≤ V_L ≤ V_{CC} ≤ +2.5 V						
t_{RVCC}	I/O V_{CC} Risetime				15	ns
t_{FVCC}	I/O V_{CC} Falltime				15	ns
t_{RVL}	I/O V_L Risetime				15	ns
t_{FVL}	I/O V_L Falltime				15	ns
$t_{PDVL−VCC}$	Propagation Delay (Driving I/O V_L)				15	ns
$t_{PDVCC−VL}$	Propagation Delay (Driving I/O V_{CC})				15	ns
t_{PPSKEW}	Part−to−Part Skew				10	nS
MDR	Maximum Data Rate		16			Mb/s
+2.5 ≤ V_L ≤ V_{CC} ≤ +3.3 V						
t_{RVCC}	I/O V_{CC} Risetime				15	ns
t_{FVCC}	I/O V_{CC} Falltime				15	ns
t_{RVL}	I/O V_L Risetime				15	ns
t_{FVL}	I/O V_L Falltime				15	ns
$t_{PDVL−VCC}$	Propagation Delay (Driving I/O V_L)				15	ns
$t_{PDVCC−VL}$	Propagation Delay (Driving I/O V_{CC})				15	ns
t_{PPSKEW}	Part−to−Part Skew				10	nS
MDR	Maximum Data Rate		20			Mb/s

3. All units are production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design.

TIMING CHARACTERISTICS − OPEN DRAIN DRIVING CONFIGURATIONS

(I/O test circuit of Figures 4 and 5, C_{LOAD} = 15 pF, driver output impedance ≤ 50 Ω, R_{LOAD} = 1 MΩ)

Symbol	Parameter	Test Conditions	−40°C to +85°C (Note 4)			Unit
			Min	Typ	Max	
+1.2 ≤ V_L ≤ V_{CC} ≤ +4.5 V						
t_{RVCC}	I/O V_{CC} Risetime				400	ns
t_{FVCC}	I/O V_{CC} Falltime				50	ns
t_{RVL}	I/O V_L Risetime				400	ns
t_{FVL}	I/O V_L Falltime				60	ns
$t_{PDVL-VCC}$	Propagation Delay (Driving I/O V_L)				1000	ns
$t_{PDVCC-VL}$	Propagation Delay (Driving I/O V_{CC})				1000	ns
t_{PPSKEW}	Part−to−Part Skew				50	nS
MDR	Maximum Data Rate		2			Mb/s

4. All units are production tested at T_A = +25°C. Limits over the operating temperature range are guaranteed by design. Limits over the operating temperature range are guaranteed by design.

TEST SETUPS

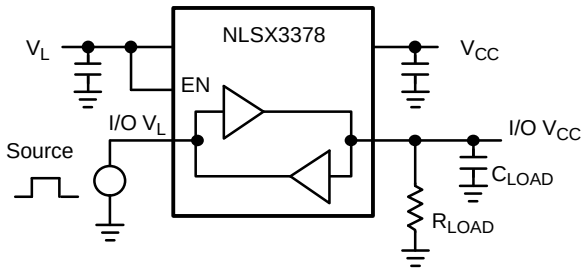


Figure 2. Rail−to−Rail Driving I/O V_L

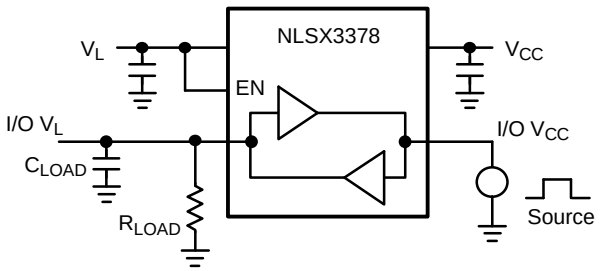


Figure 3. Rail−to−Rail Driving I/O V_{CC}

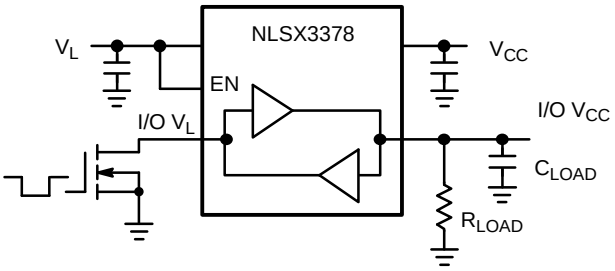


Figure 4. Open−Drain Driving I/O V_L

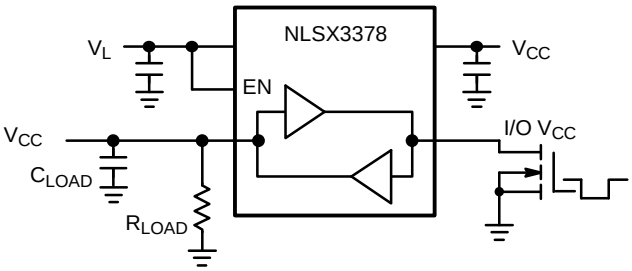


Figure 5. Open−Drain Driving I/O V_{CC}

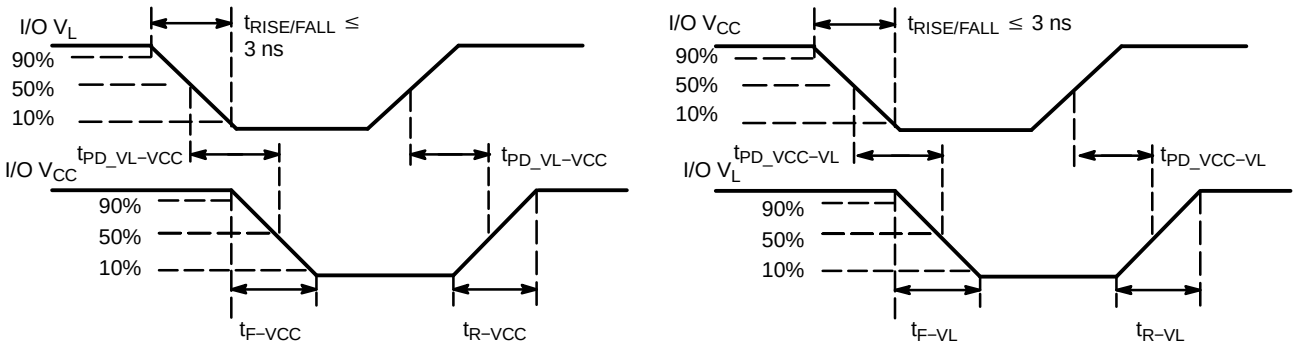
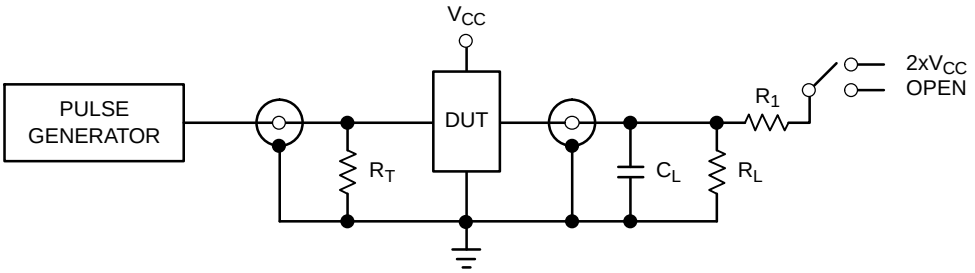


Figure 6. Definition of Timing Specification Parameters



Test	Switch
t_{PZH}, t_{PHZ}	Open
t_{PZL}, t_{PLZ}	2 x V_{CC}

C_L = 15 pF or equivalent (Includes jig and probe capacitance)
R_L = R_1 = 50 kΩ or equivalent
R_T = Z_{OUT} of pulse generator (typically 50 Ω)

Figure 7. Test Circuit for Enable/Disable Time Measurement

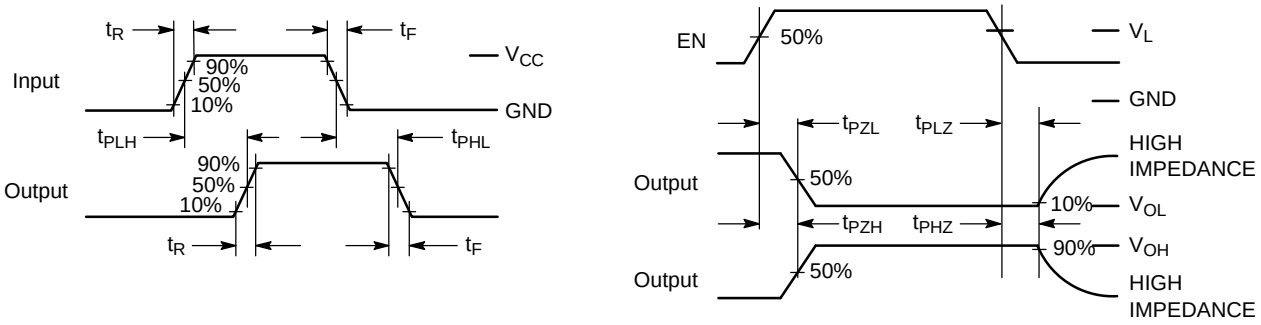


Figure 8. Timing Definitions for Propagation Delays and Enable/Disable Measurement

APPLICATIONS INFORMATION

Level Translator Architecture

The NLSX3378 auto sense translator provides bi−directional voltage level shifting to transfer data in multiple supply voltage systems. This device has two supply voltages, V_L and V_{CC}, which set the logic levels on the input and output sides of the translator. When used to transfer data from the V_L to the V_{CC} ports, input signals referenced to the V_L supply are translated to output signals with a logic level matched to V_{CC}. In a similar manner, the V_{CC} to V_L translation shifts input signals with a logic level compatible to V_{CC} to an output signal matched to V_L.

The NLSX3378 consists of two bi−directional channels that independently determine the direction of the data flow without requiring a directional pin. The one−shot circuits are used to detect the rising or falling input signals. In addition, the one shots decrease the rise and fall time of the output signal for high−to−low and low−to−high transitions.

Each input/output channel has an internal 10 kΩ pull. The magnitude of the pullup resistors can be reduced by connecting external resistors in parallel to the internal 10 kΩ resistors.

Input Driver Requirements

The rise (t_R) and fall (t_F) timing parameters of the open drain outputs depend on the magnitude of the pull−up resistors. In addition, the propagation times (t_{PD}), skew (t_{PSKEW}) and maximum data rate depend on the impedance of the device that is connected to the translator. The timing parameters listed in the data sheet assume that the output impedance of the drivers connected to the translator is less than 50 kΩ.

Enable Input (EN)

The NLSX3378 has an Enable pin (EN) that provides tri−state operation at the I/O pins. Driving the Enable pin to a low logic level minimizes the power consumption of the device and drives the I/O V_{CC} and I/O V_L pins to a high impedance state. Normal translation operation occurs when the EN pin is equal to a logic high signal. The EN pin is referenced to the V_L supply and has Overvoltage Tolerant (OVT) protection.

Power Supply Guidelines

During normal operation, supply voltage V_L should be less than or equal to V_{CC}. The sequencing of the power supplies will not damage the device during the power up operation.

The enable pin should be used to enter the low current tri−state mode, rather than setting either the V_L or V_{CC} supplies to 0 V. The NLSX3378 will not be damaged if either V_L or V_{CC} is equal to 0 V while the other supply voltage is at a nominal operating value; however, the operation of the translator cannot be guaranteed during single supply operation.

For optimal performance, 0.01 μF to 0.1 μF decoupling capacitors should be used on the V_L and V_{CC} power supply pins. Ceramic capacitors are a good design choice to filter and bypass any noise signals on the voltage lines to the ground plane of the PCB. The noise immunity will be maximized by placing the capacitors as close as possible to the supply and ground pins, along with minimizing the PCB connection traces.

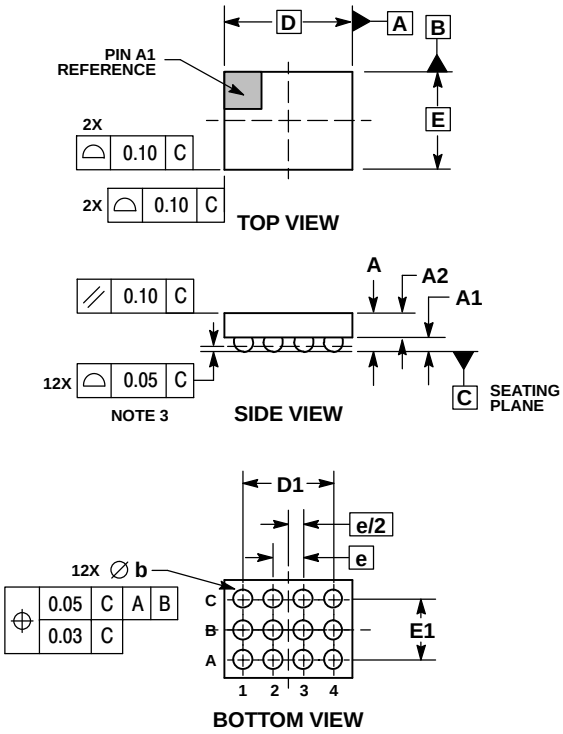
ORDERING INFORMATION

Device	Package	Shipping†
NLSX3378FCT1G	μBump12 (Pb−Free)	3000 / Tape & Reel
NLSX3378BFCT1G	μBump12 (Backside Laminate Coating) (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

μBump12, 2.02x1.54, 0.5P
CASE 499AU−01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.

	MILLIMETERS	
DIM	MIN	MAX
A	−−−	0.66
A1	0.21	0.27
A2	0.33	0.39
b	0.29	0.34
D	2.02 BSC	
D1	1.50 BSC	
E	1.54 BSC	
E1	1.00 BSC	
e	0.50 BSC	

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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NLSX3378/D